

### **General Description**

The WSF15P10 is the highest performance trench P-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSF15P10 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

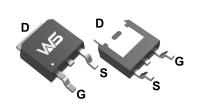
### **Product Summery**

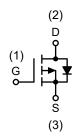
BVDSS	RDSON	ID
-100V	150mΩ	-13A

## **Applications**

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

## **TO-252-2L Pin Configuration**





### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-100	V
$V_{GS}$	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, -V <sub>GS</sub> @ -10V <sup>1</sup>	-13	Α
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, -V <sub>GS</sub> @ -10V <sup>1</sup>	-7	Α
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-45	Α
EAS	Single Pulse Avalanche Energy <sup>3</sup>	25	mJ
I <sub>AS</sub>	Avalanche Current	-10	Α
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation⁴	50	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	$^{\circ}$
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>		50	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case <sup>1</sup>		2.5	°C/W



## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-100			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25℃, I <sub>D</sub> =-1mA		-0.021		V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V , I <sub>D</sub> =-5.5A		150	205	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1		-3	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	VGS-VDS , ID230UA		4.08		mV/℃
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =-48V , $V_{GS}$ =0V , $T_J$ =25 $^{\circ}$ C			1	uA
DSS	Dialii-Source Leakage Current	$V_{DS}$ =-48V , $V_{GS}$ =0V , $T_J$ =55 $^{\circ}$ C			5	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm 20V$ , $V_{DS}$ = $0V$			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =-10V , I <sub>D</sub> =-6A		8		S
$Q_g$	Total Gate Charge (-4.5V)			21		
$Q_gs$	Gate-Source Charge	V <sub>DS</sub> =-50V , V <sub>GS</sub> =-10V , I <sub>D</sub> =-5.5A		4.3		nC
$Q_gd$	Gate-Drain Charge			5.2		
$T_{d(on)}$	Turn-On Delay Time			11	23	
Tr	Rise Time	$V_{DD}$ =-30V , $V_{GS}$ =-10V , $R_{G}$ =6 $\Omega$ ,		10	20	ns
$T_{d(off)}$	Turn-Off Delay Time	I <sub>D</sub> =-1A ,RG=30Ω.		55	120	115
T <sub>f</sub>	Fall Time			30	65	
C <sub>iss</sub>	Input Capacitance			1050	1500	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-30V , V <sub>GS</sub> =0V , f=1MHz		70	100	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			30	55	

## **Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =-25V , L=0.5mH , I <sub>AS</sub> =-10A	20			mJ

### **Diode Characteristics**

Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-15	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}$ =0 $V$ , $I_{S}$ =-1 $A$ , $T_{J}$ =25 $^{\circ}$ C			-1.3	V

#### Note

- 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, t≤10sec.
- 2.The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%
- 3. The EAS data shows Max. rating . The test condition is  $V_{DD}$ =-25V,  $V_{GS}$ =-10V, L=0.5mH,  $I_{AS}$ =-10A
- 4.The power dissipation is limited by 150 ℃ junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



### Typical Characteristics

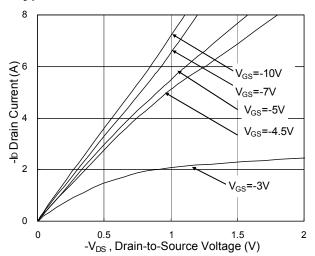


Fig.1 Typical Output Characteristics

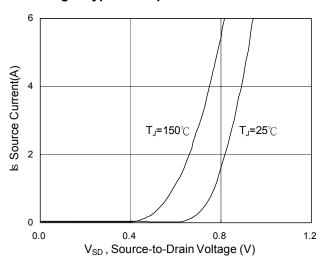


Fig.3 Forward Characteristics Of Reverse

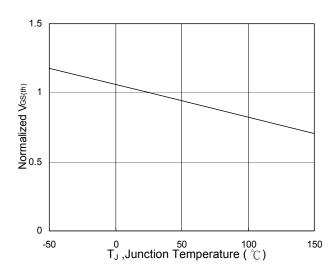


Fig.5 Normalized V<sub>GS(th)</sub> v.s T<sub>J</sub>

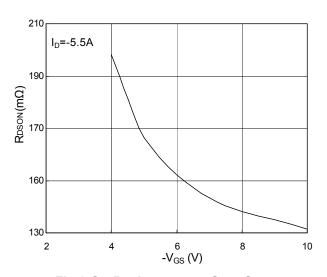


Fig.2 On-Resistance v.s Gate-Source

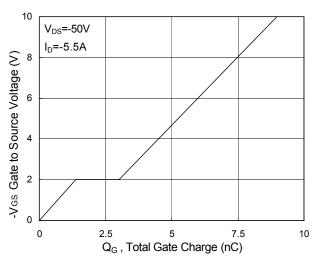


Fig.4 Gate-Charge Characteristics

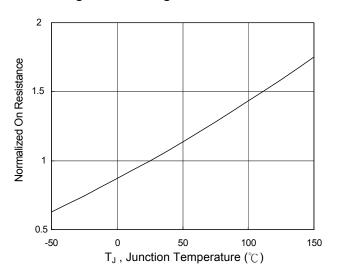
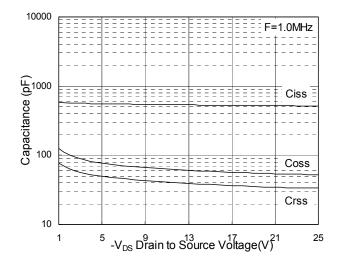


Fig.6 Normalized R<sub>DSON</sub> v.s T<sub>J</sub>







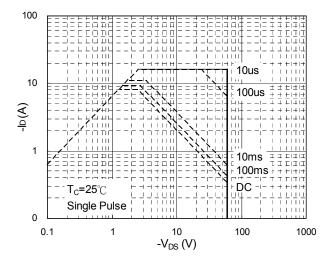


Fig.7 Capacitance

Fig.8 Safe Operating Area

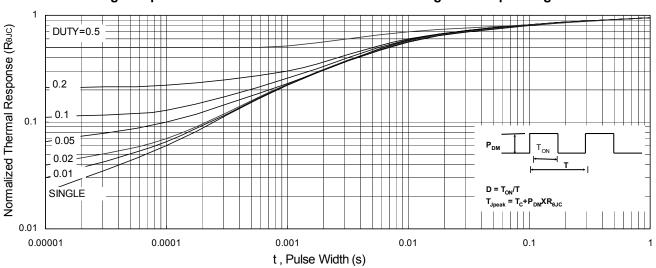


Fig.9 Normalized Maximum Transient Thermal Impedance

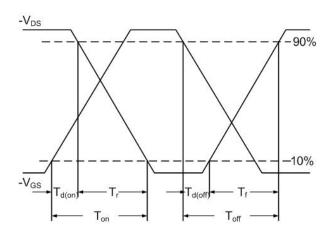


Fig.10 Switching Time Waveform

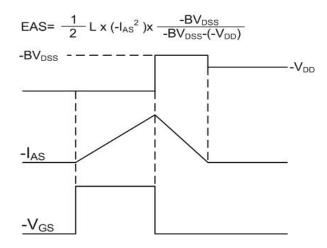
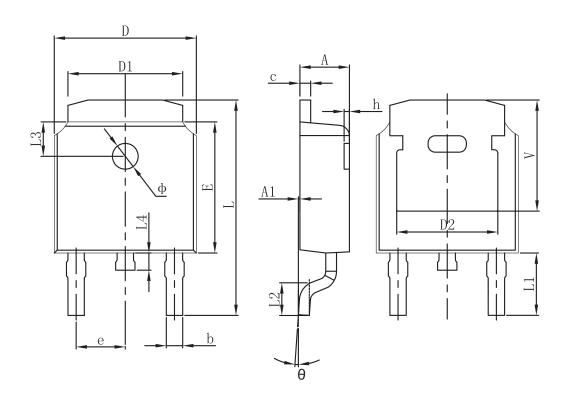


Fig.11 Unclamped Inductive Waveform



# **Packaging information**



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 REF.		0.190 REF.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900 REF.		0.114	REF.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063	REF.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	REF.	0.207 REF.		



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